

# **Phase Control Thyristor**

DS6023 -1 April 2011 (LN28234)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

# **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR3710V14 DCR3710V12 DCR3710V10 DCR3710V08 DCR3710V06	1400 1200 1000 800 600	$\begin{split} T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} = I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM}  t_p = 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} = \\ V_{DRM}  \&  V_{RRM}  +100V \\ respectively \end{split}$

Lower voltage grades available.

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR3710V14

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

#### **KEY PARAMETERS**

$V_{DRM}$	1400 V
$I_{T(AV)}$	3710 A
I <sub>TSM</sub>	60000 A
dV/dt*	1000 V/µs
dI/dt	200 A/μs

# \* Higher dV/dt selections available

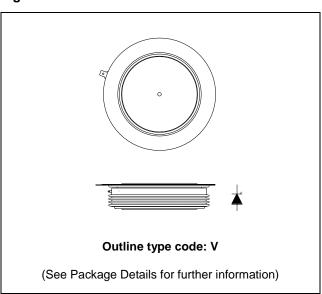


Fig. 1 Package outline



# **CURRENT RATINGS**

# $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions		Units	
Double Si	Double Side Cooled				
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	3710	А	
I <sub>T(RMS)</sub>	RMS value	-	5820	А	
Ι <sub>Τ</sub>	Continuous (direct) on-state current	-	5250	А	

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	60.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	18.00	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.01	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Double side cooled	DC	-	0.003	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / <sub>VRRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-40	140	°C
F <sub>m</sub>	Clamping force			50	62	kN



# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, gate open		-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 5000A	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, $10\Omega$ ,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V <sub>T</sub>	On-state voltage	I <sub>T</sub> = 3000A, T <sub>case</sub> = 125°C			1.12	V
V <sub>T(TO)</sub>	Threshold	T <sub>case</sub> = 125°C		-	0.83	V
r <sub>T</sub>	On-state slope resistance	T <sub>case</sub> = 125°C		-	0.092	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3.0	μs
	,	$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 10$ A/ $\mu$ s,		-	300	μs
		dV <sub>DR</sub> /dt = 20V/μs linear to 67% V <sub>DRM</sub>				
Qs	Stored charge	$I_T = 4000A$ , tp = 1000us, $T_j = 125$ °C, dl/dt =10A/ $\mu$ s,		-	2600	μC
I <sub>RR</sub>	Reverse recovery current			-	170	Α
IL	Latching current	$T_j = 25$ °C,		-	1	Α
I <sub>H</sub>	Holding current	$T_j = 25$ °C,		-	200	mA

# **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter Test Conditions		Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	3	V
$V_{GD}$	Gate non-trigger voltage	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	300	mA
I <sub>GD</sub>	Gate non-trigger current	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	mA



#### **CURVES**

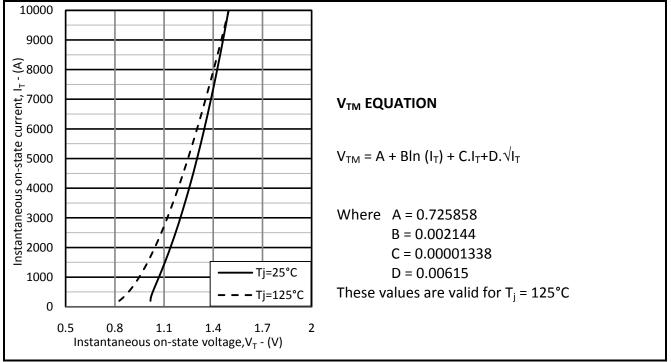


Fig.2 Maximum &minimum on-state characteristics

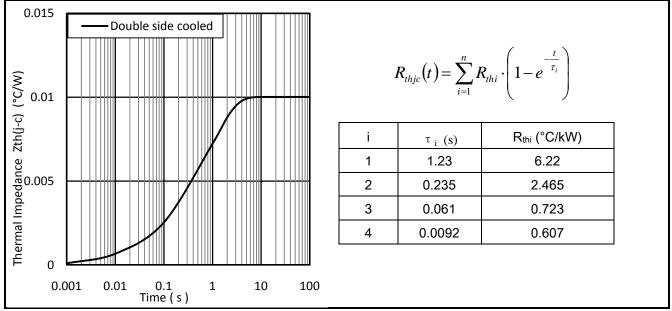
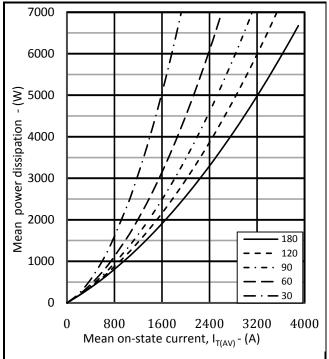


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)





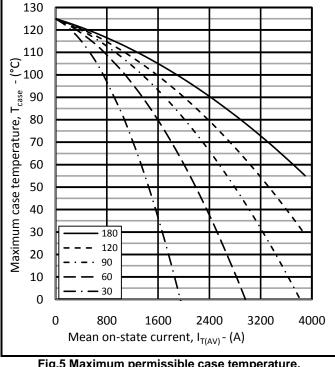


Fig.4 On-state power dissipation – sine wave

Fig.5 Maximum permissible case temperature, double side cooled – sine wave

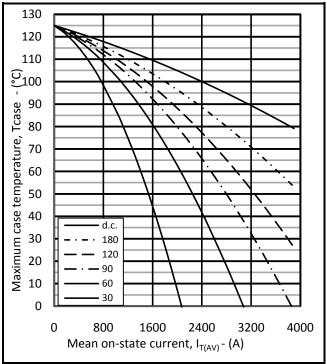


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

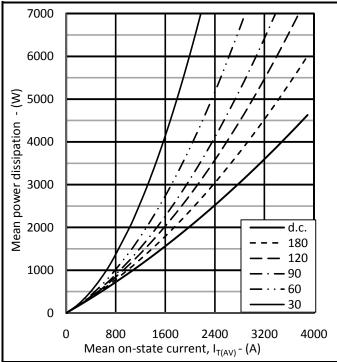
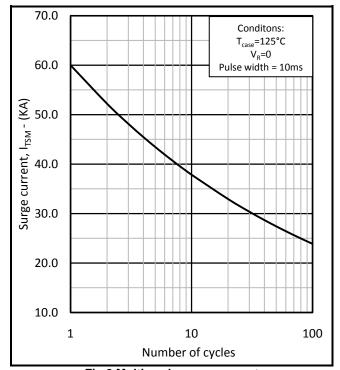
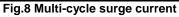


Fig.7 On-state power dissipation - rectangular wave







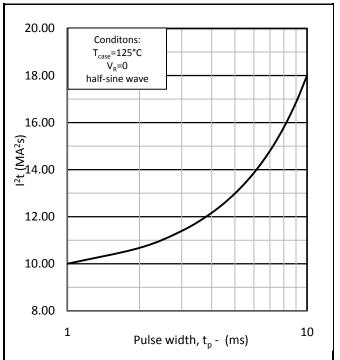


Fig.9 Single-cycle I2t

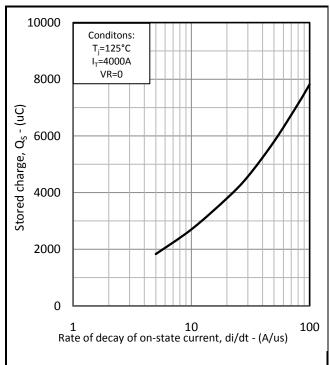


Fig.10 Stored charge vs di/dt

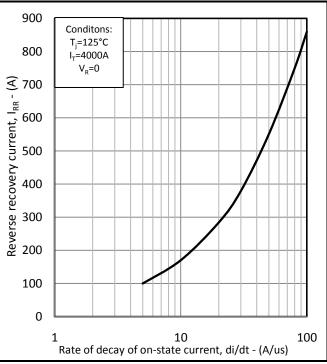


Fig.11 Reverse recovery current vs di/dt



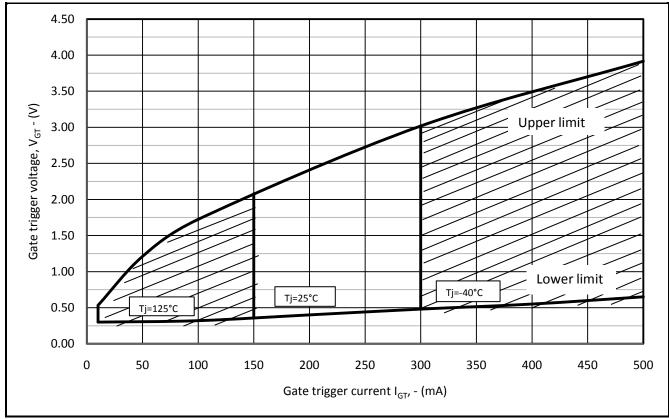


Fig.12 Gate characteristics

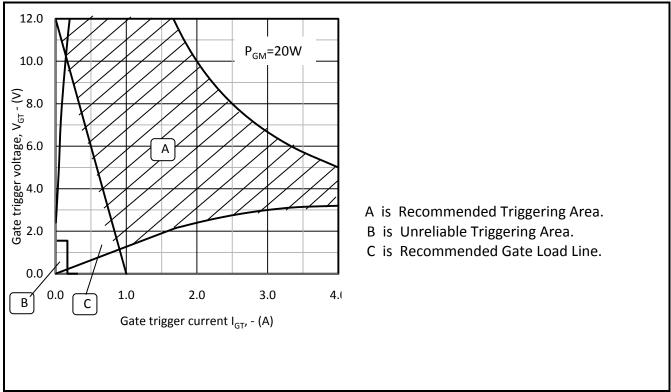


Fig.13 Gate characteristics



#### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

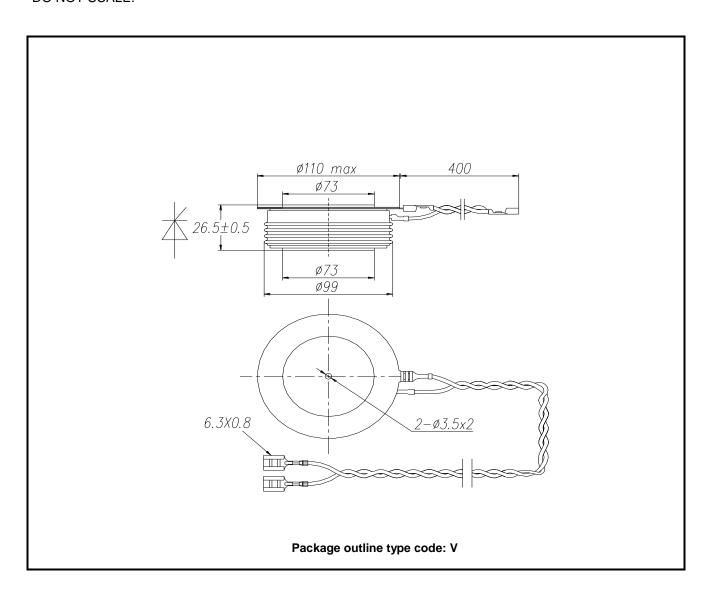


Fig.14 Package outline



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